



1Mbit/s High Speed Phototransistor Optocoupler

www.ct-micro.com

Features

- High speed 1MBit/s
- High isolation voltage between input and output (Viso=5000 Vrms)
- Operating emperature range -55°C to 100°C
- MSL class 1
- Regulatory Approvals
 - ✓ UL - UL1577 (E364000)
 - ✓ VDE - EN60747-5-5(VDE0884-5)
 - ✓ CQC – GB4943.1, GB8898(14001104779)
 - ✓ IEC62368 (FI/41119)

Applications

- Line receivers
- Telecommunication equipment
- High speed logic ground isolation
- Feedback loop in switch-mode power supplies

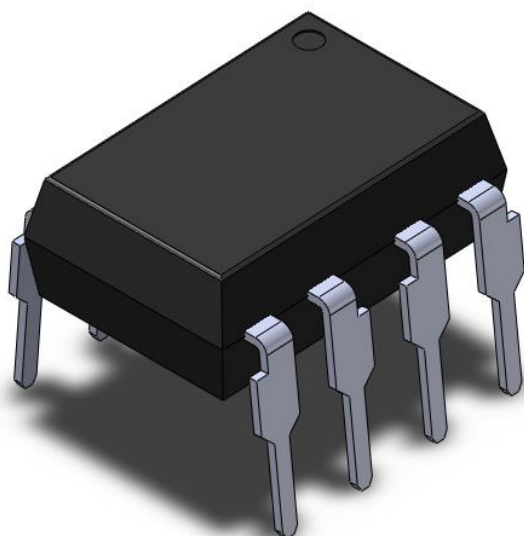
- Home appliances

Description

The CT4505 devices each consist of an infrared emitting diode, optically coupled to a high speed photo detector transistor. A separate connection for the photodiode bias and output-transistor collector increase the speed by several orders of magnitude over conventional phototransistor couplers by reducing the base-collector capacitance of the input transistor.

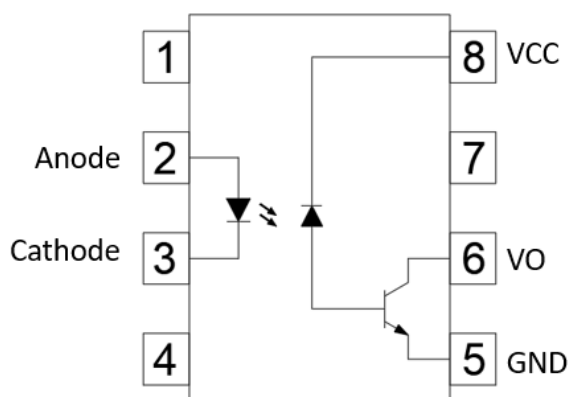
The devices are packaged in an 8-pin DIP package and also available in gullwing (400mil) and surface mount lead forming.

Package Outline



Note: Different bending options available. See package dimension.

Schematic





1Mbit/s High Speed Phototransistor Optocoupler

www.ct-micro.com**Absolute Maximum Ratings** $T_A = 25^\circ\text{C}$, unless otherwise specified

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameters	Ratings	Units	Notes
V _{ISO}	Isolation voltage (AC, 1 minute, 40 ~ 60% R.H.)	5000	V _{RMS}	1
T _{OPR}	Operating temperature	-55 ~ +100	°C	
T _{STG}	Storage temperature	-55 ~ +125	°C	
T _{SOL}	Soldering temperature (For 10 seconds)	260	°C	2
Emitter				
I _F	Forward current	25	mA	
I _{FP}	Peak forward current (50% duty, 1ms P.W)	50	mA	
I _{F(TRANS)}	Peak transient current (≤1μs P.W,300pps)	1	A	
V _R	Reverse voltage	5	V	
P _D	Power dissipation	40	mW	
Detector				
P _D	Power dissipation	100	mW	
I _{O(AVG)}	Average Output current	8	mA	
I _{O(Peak)}	Peak Output current	16	mA	
V _O	Output voltage	-0.5 to 20	V	
V _{CC}	Supply voltage	-0.5 to 30	V	

**Electrical Characteristics** *Typical values are measured at $T_A = 25^\circ\text{C}$* **Emitter Characteristics**

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
V_F	Forward voltage	$I_F = 16\text{mA}$	-	1.5	1.8	V	
V_R	Reverse voltage	$I_R = 10\mu\text{A}$	5.0	-	-	V	
$\Delta V_F / \Delta T_A$	Temperature coefficient of forward voltage	$I_F = 16\text{mA}$	-	-1.8	-	mV/ $^\circ\text{C}$	
C_T	Input capacitance	$V_F = 0, f = 1\text{MHz}$		12		pF	

Detector Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
I_{OH}	Logic High Output current	$I_F = 0\text{mA}, V_O = V_{CC} = 5.5\text{V},$ $T_A = 25^\circ\text{C}$	-	-	0.5	μA	
		$I_F = 0\text{mA}, V_{CC} = 30\text{V},$ $V_O = 20\text{V}, T_A = 25^\circ\text{C}$	-	-	5		
		$I_F = 0\text{mA}, V_{CC} = 30\text{V},$ $V_O = 20\text{V}, T_A = 70^\circ\text{C}$	-	-	50		
I_{CCL}	Logic Low Supply current	$I_F = 10\text{mA}, V_O = \text{Open},$ $V_{CC} = 30\text{V}$	-	-	200	μA	
I_{CCH}	Logic High Supply current	$I_F = 0\text{mA}, V_O = \text{Open}, V_{CC} = 30\text{V}$	-	-	1	μA	

Transfer Characteristics

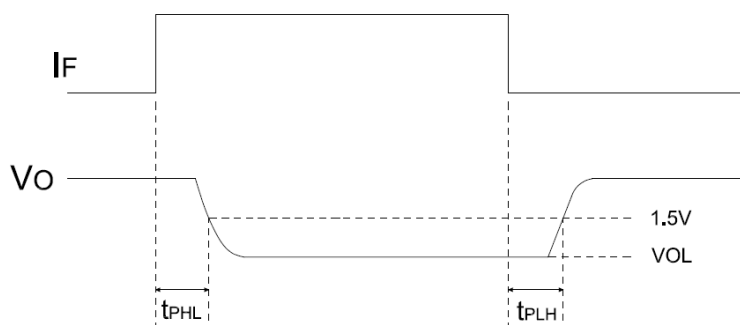
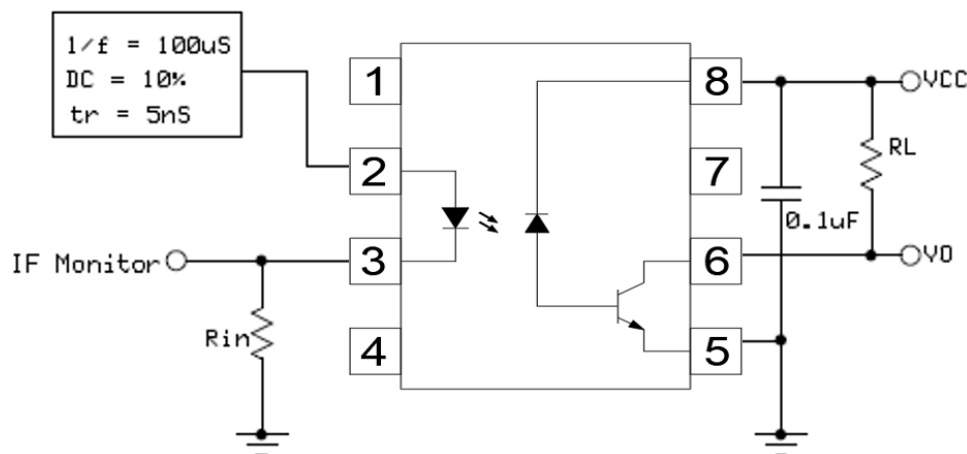
Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
CTR	Current Transfer Ratio	$I_F = 10\text{mA}, V_O = 0.4\text{V}, V_{CC} = 4.5\text{V},$ $T_A = 25^\circ\text{C}$	25	-	75	%	
		$I_F = 16\text{mA}, V_O = 0.4\text{V}, V_{CC} = 4.5\text{V},$ $T_A = -25 \sim 100^\circ\text{C}$	15	-	-		
V_{OL}	Logic Low Output voltage	$I_F = 16\text{mA}, I_O = 2.4\text{mA},$ $V_{CC} = 4.5\text{V}$	-	-	0.4	V	
C_S	Capacitance input to output	$V_F = 0, f = 1\text{MHz}$		1.1		pF	

**Electrical Characteristics** *Typical values are measured at $T_A = 25^\circ\text{C}$* **Switching Characteristics**

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
T_{PHL}	Propagation Delay Time Logic High to Logic Low	$I_F = 10\text{mA}$, $V_{CC} = 15\text{V}$, $R_L = 20\text{K}\Omega$, $T_A = 25^\circ\text{C}$	0.1	0.45	0.8	μs	
		$I_F = 10\text{mA}$, $V_{CC} = 15\text{V}$, $R_L = 20\text{K}\Omega$, $T_A = 0 \sim 85^\circ\text{C}$	0.1	-	1.9		
		$I_F = 10\text{mA}$, $V_{CC} = 15\text{V}$, $R_L = 20\text{K}\Omega$, $T_A = -25 \sim 100^\circ\text{C}$	0.1	-	2.0		
T_{PLH}	Propagation Delay Time Logic Low to Logic High	$I_F = 10\text{mA}$, $V_{CC} = 15\text{V}$, $R_L = 20\text{K}\Omega$, $T_A = 25^\circ\text{C}$	0.1	0.45	0.8	μs	
		$I_F = 10\text{mA}$, $V_{CC} = 15\text{V}$, $R_L = 20\text{K}\Omega$, $T_A = 0 \sim 85^\circ\text{C}$	0.1	-	1.9		
		$I_F = 10\text{mA}$, $V_{CC} = 15\text{V}$, $R_L = 20\text{K}\Omega$, $T_A = -25 \sim 100^\circ\text{C}$	0.1	-	2.0		
$ T_{PHL} - T_{PLH} $	Pulse width distortion	$I_F = 10\text{mA}$, $V_{CC} = 15\text{V}$, $R_L = 20\text{K}\Omega$		0.25	0.8	μs	
		$I_F = 10\text{mA}$, $V_{CC} = 15\text{V}$, $R_L = 20\text{K}\Omega$, $T_A = 0 \sim 85^\circ\text{C}$			1.7		
		$I_F = 10\text{mA}$, $V_{CC} = 15\text{V}$, $R_L = 20\text{K}\Omega$, $T_A = -25 \sim 100^\circ\text{C}$			1.8		
CM_H	Common Mode Transient Immunity at Logic High	$I_F = 0\text{mA}$, $V_{CM} = 1500\text{Vp-p}$, $R_L = 20\text{K}\Omega$, $T_A = 25^\circ\text{C}$	15,000			$\text{V}/\mu\text{s}$	
CM_L	Common Mode Transient Immunity at Logic Low	$I_F = 16\text{mA}$, $V_{CM} = 1500\text{Vp-p}$, $R_L = 20\text{K}\Omega$, $T_A = 25^\circ\text{C}$	15,000			$\text{V}/\mu\text{s}$	



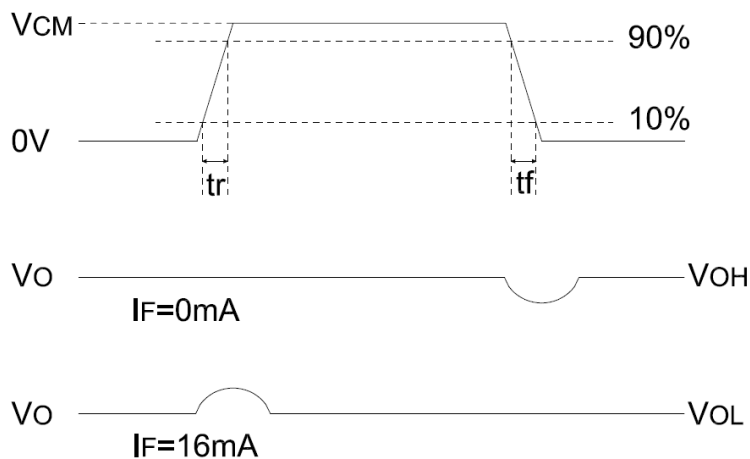
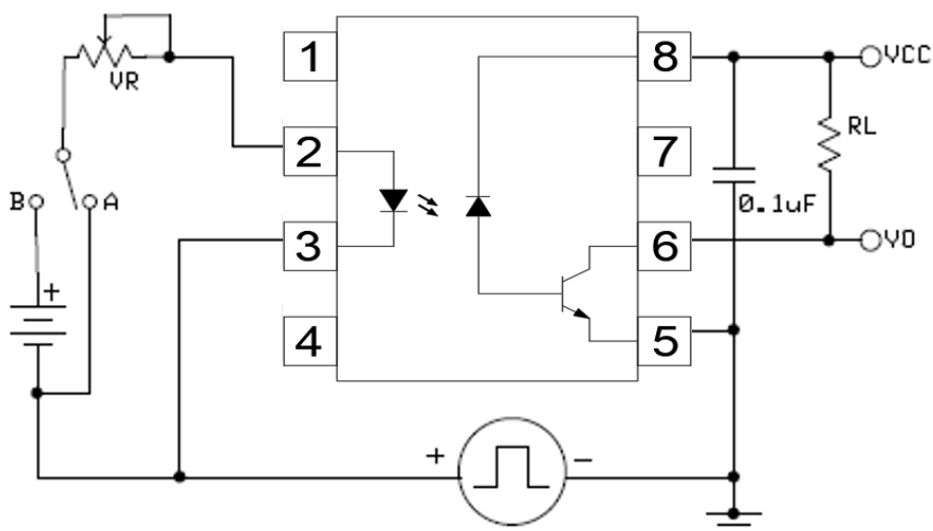
Test Circuits



Switching Time Test Circuits



Test Circuits

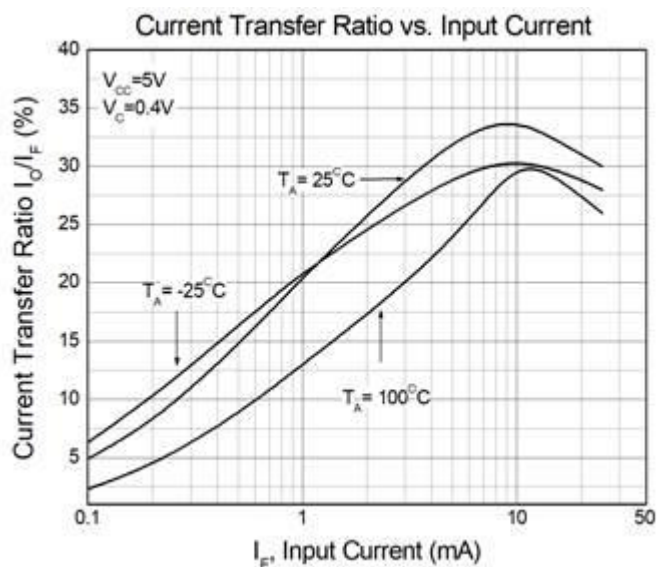


CMR Test Circuits



1Mbit/s High Speed Phototransistor Optocoupler

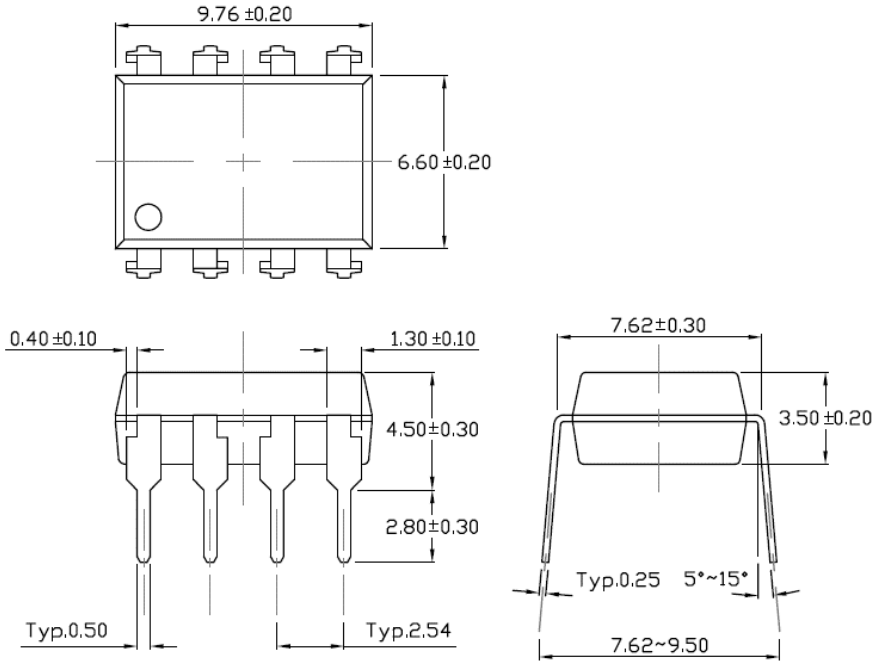
Test Circuits



CTR Test Circuits

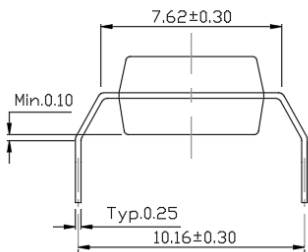


Package Dimension *Dimensions in mm unless otherwise stated*

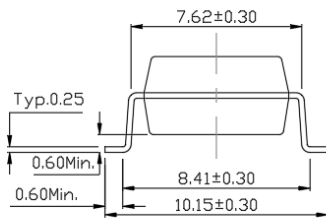


Package Dimension *Dimensions in mm unless otherwise stated*

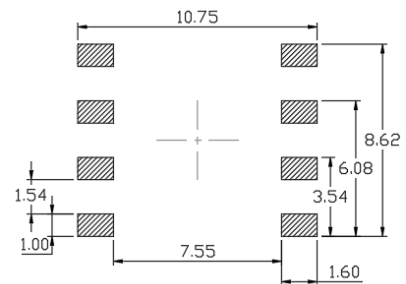
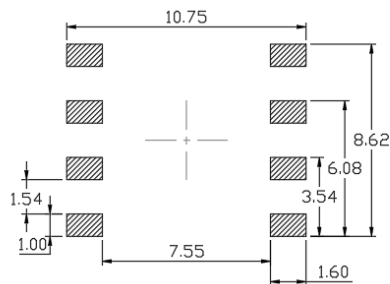
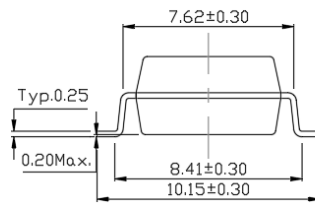
M Type



S Type

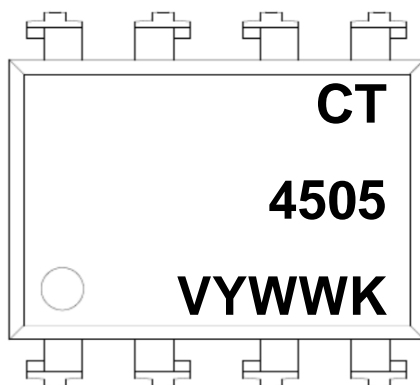


SL Type





Marking Information



Note:

- CT : Denotes “CT Micro”
- 4503 : Part Number
- V : VDE Safety Mark Option (Blank or V)
- Y : One Digit Year Code
- WW : Two Digit Work Week
- K : Manufacturing Code

Ordering Information

CT4505(V)(Y)(Z)

V = VDE Option (V or None)

Y = Lead form option (S, SL, M or none)

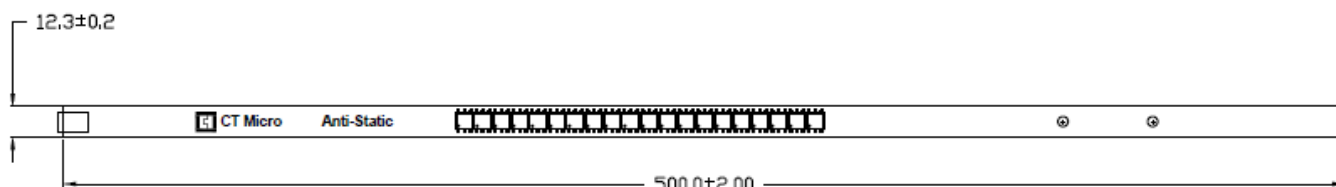
Z = Tape and reel option (T1, T2 or none)

Option	Description	Quantity
None	Standard 8 Pin Dip	40 Units/Tube
M	Gullwing (400mil) Lead Forming	40 Units/Tube
S(T1)	Surface Mount Lead Forming – With Option 1 Taping	1000 Units/Reel
S(T2)	Surface Mount Lead Forming – With Option 2 Taping	1000 Units/Reel
SL(T1)	Surface Mount (Low Profile) Lead Forming– With Option 1 Taping	1000 Units/Reel
SL(T2)	Surface Mount (Low Profile) Lead Forming– With Option 2 Taping	1000 Units/Reel



Carrier Specifications *Dimensions in mm unless otherwise stated*

Tube Option Standard DIP

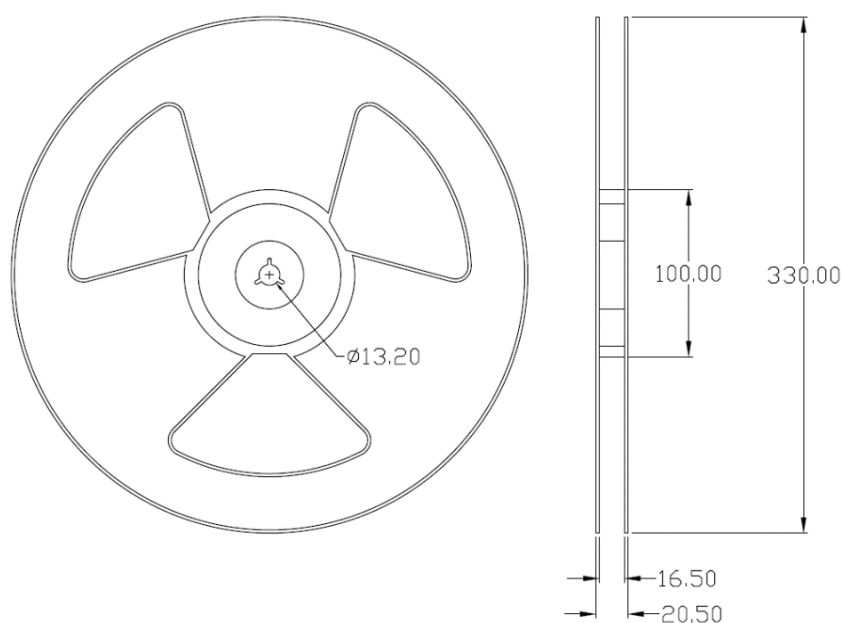


Tube Option M Type



Reel Dimension *All dimensions are in mm, unless otherwise stated*

Option S(T1/T2) & SL(T1/T2)





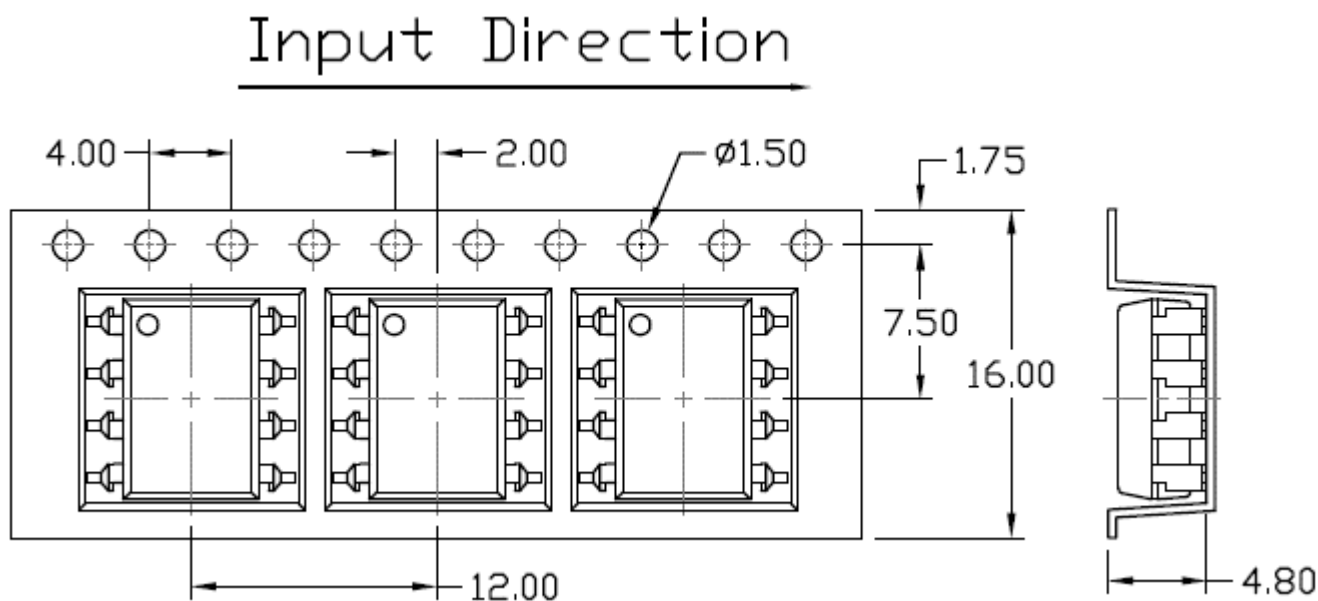
CT4505

1Mbit/s High Speed Phototransistor Optocoupler

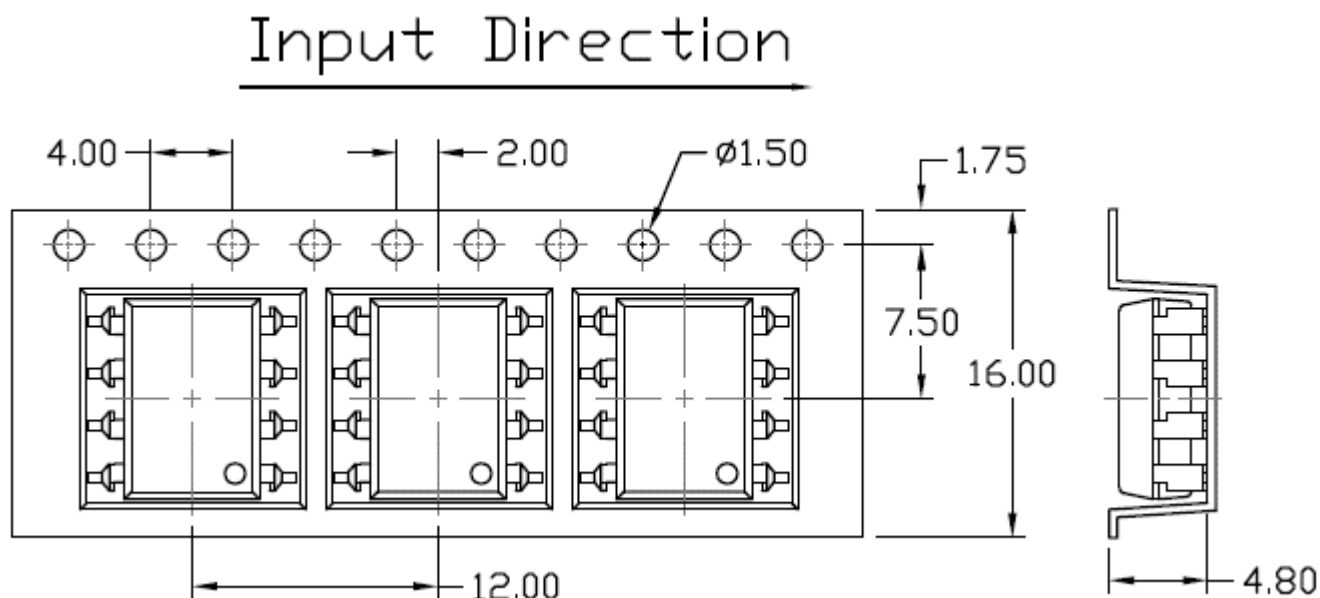
www.ct-micro.com

Carrier Tape Specifications *Dimensions in mm unless otherwise stated*

Option S(T1) & SL(T1)



Option S(T2) & SL(T2)





Solderability spec (Follow the JEDEC standard JESD22-B102)

Reflow Soldering: Immersed surface, other than the end of pin as cut-surface, must be covered by solder.

Solder-Bath: More than 95% of the electrode must be covered with solder.

Wave soldering (Follow the JEDEC standard JESD22-A111)

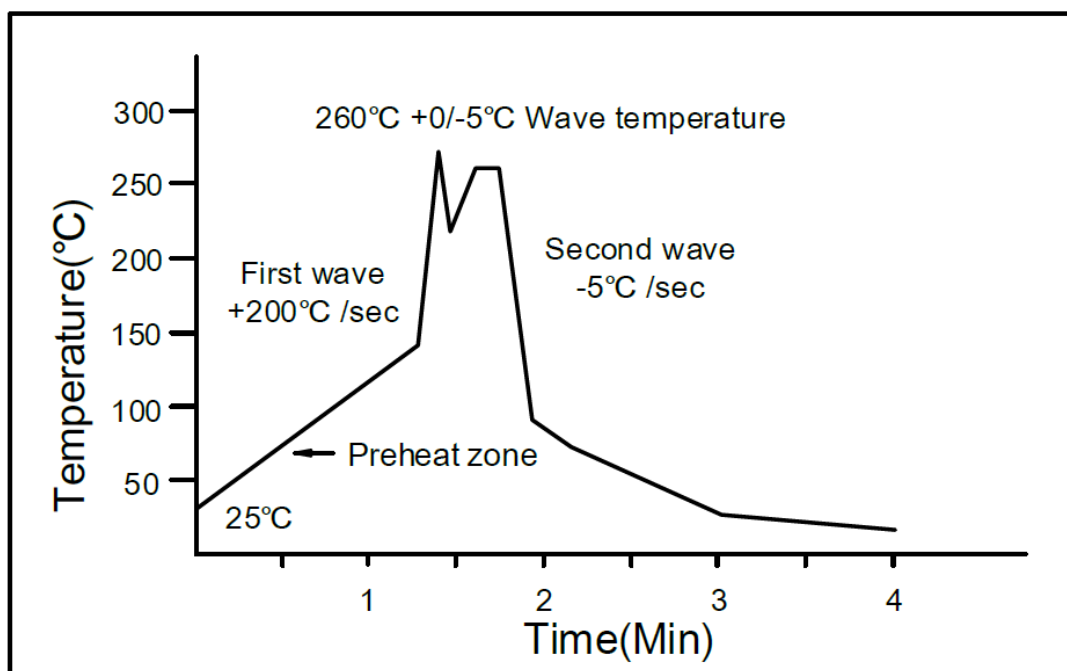
One time soldering is recommended within the condition of temperature.

Temperature: $260 \pm 0/-5^\circ\text{C}$.

Time: 10 sec.

Preheat temperature: 25 to 140°C .

Preheat time: 30 to 80 sec.



Iron soldering (Follow the standard MIL-STD 202G, Method 210F)

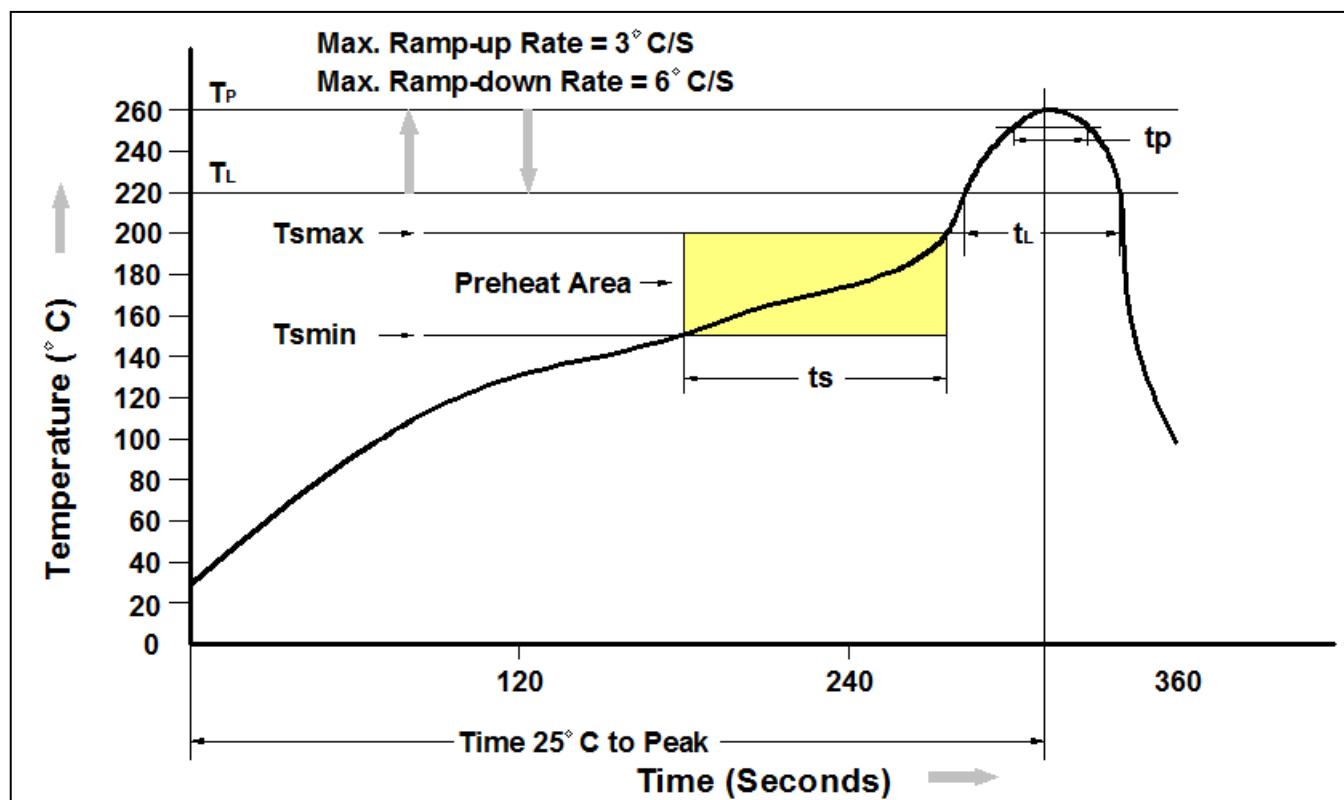
Allow single lead soldering in every single process.

One time soldering is recommended. Temperature: $350 \pm 10^\circ\text{C}$

Time: 5 sec max.



Reflow Profile (Follow the JEDEC standard J-STD-020)



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (ts) from (Tsmmin to Tsmax)	60-120 seconds
Ramp-up Rate (tL to tp)	3°C/second max.
Liquidous Temperature (TL)	217°C
Time (tL) Maintained Above (TL)	60 – 150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (tp) within 5°C of 260°C	30 seconds
Ramp-down Rate (TP to TL)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.



1Mbit/s High Speed Phototransistor Optocoupler

DISCLAIMER

CT MICRO RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. CT MICRO DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

DISCOLORATION MIGHT OCCUR ON THE PACKAGE SURFACE AFTER SOLDERING, REFLOW OR LONG TERM USE. THIS DOES NOT IMPACT THE PRODUCT PERFORMANCE NOR THE PRODUCT RELIABILITY.

CT MICRO ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT EXPRESS WRITTEN APPROVAL OF CT MICRO INTERNATIONAL CORPORATION.

- 1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instruction for use provided in the labelling, can be reasonably expected to result in significant injury to the user.*
- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.*